

**TMN3070NF****N-Channel Enhancement Mosfet****General Description**

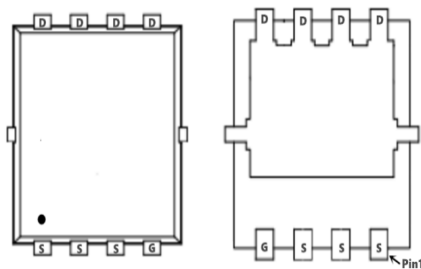
- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

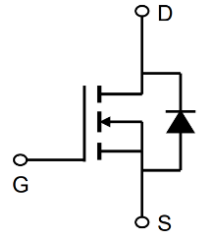
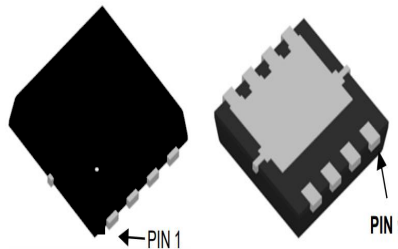
General Features $V_{DS} = 30V$ $I_D = 70A$ $R_{DS(ON)} = 5.2m\Omega$ (typ.) @ $V_{GS} = 10V$

100% UIS Tested

100% R_g Tested

Marking: 70N03

NF:DFN5x6-8L

**Absolute Maximum Ratings** ($T_A = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	± 20		V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	70		A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	60		A
I_{DM}	Pulsed Drain Current ²	192		A
EAS	Single Pulse Avalanche Energy ³	306		mJ
I_{AS}	Avalanche Current	53.8		A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	82.5		W
T_{STG}	Storage Temperature Range	-55 to 175		$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175		$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.56	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case ^(Note 2)	---	1.8	$^\circ C/W$



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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	5.2	6.5	mΩ
		V _{GS} =5V, I _D =24A	-	7.5	10	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =24A	20	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	2016	-	PF
Output Capacitance	C _{OSS}		-	251	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	230	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V, I _D =30A V _{GS} =10V, R _{GEN} =2.7Ω	-	20	-	nS
Turn-on Rise Time	t _r		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	60	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =10V, I _D =30A, V _{GS} =10V	-	60.5	-	nC
Gate-Source Charge	Q _{gs}		-	8.1	-	nC
Gate-Drain Charge	Q _{gd}		-	7.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =24A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	70	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 80A di/dt = 100A/μs (Note3)	-	32	50	nS
Reverse Recovery Charge	Q _{rr}		-	12	20	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition: T_J=25°C, V_{DD}=15V, V_G=10V, L=0.5mH, R_G=25Ω, I_{AS}=35A

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Typical Electrical and Thermal Characteristics (Curves)

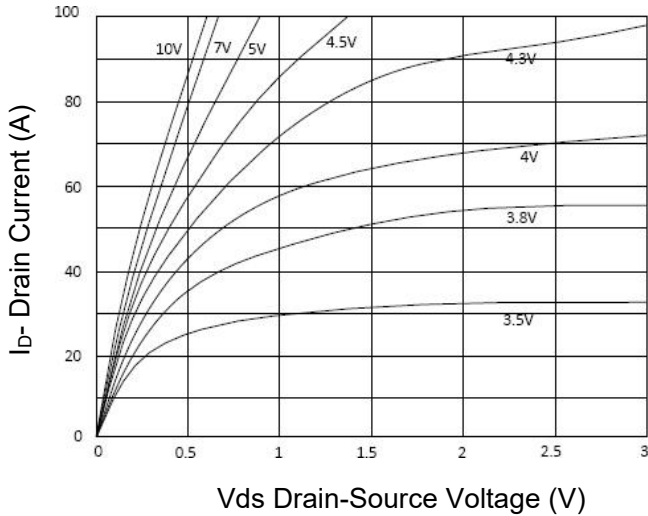


Figure 1 Output Characteristics

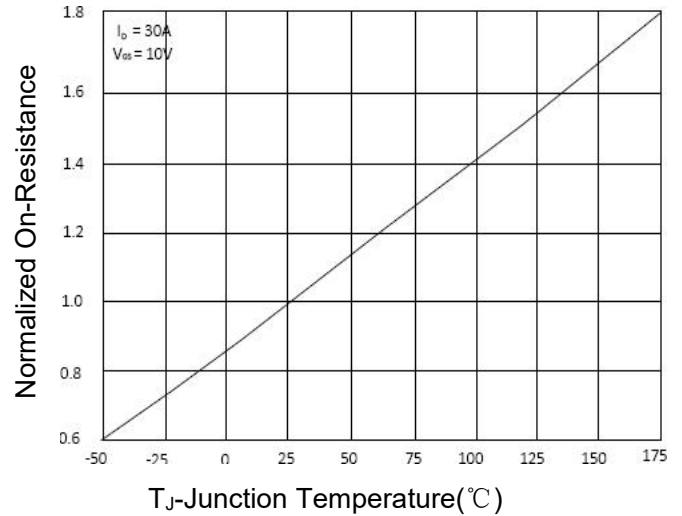


Figure 4 Rdson-Junction Temperature

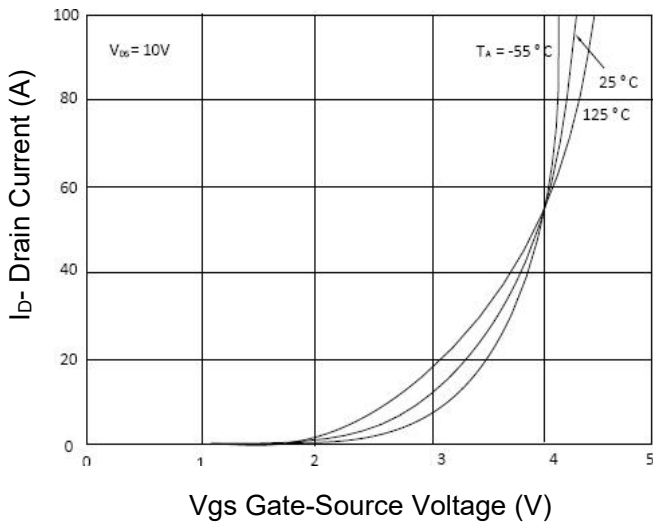


Figure 2 Transfer Characteristics

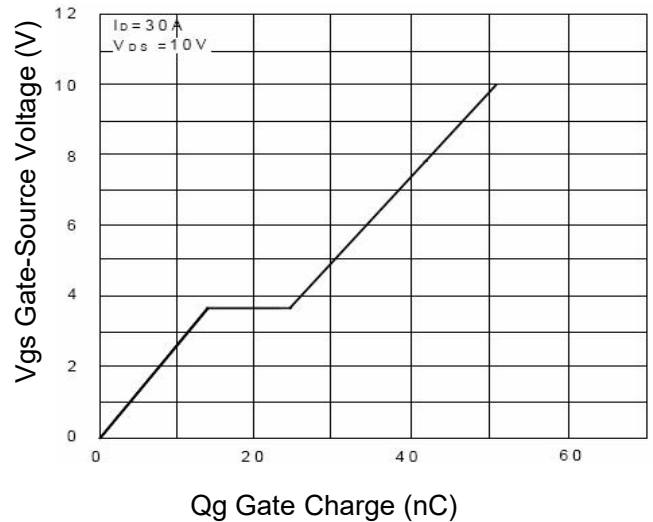


Figure 5 Gate Charge

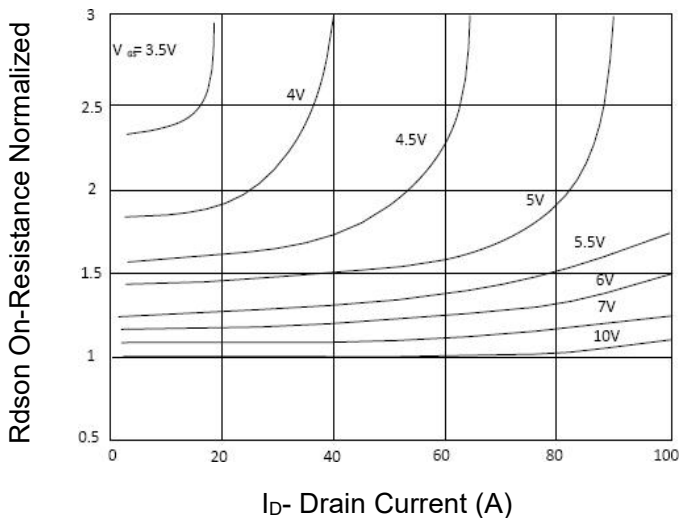


Figure 3 Rdson- Drain Current

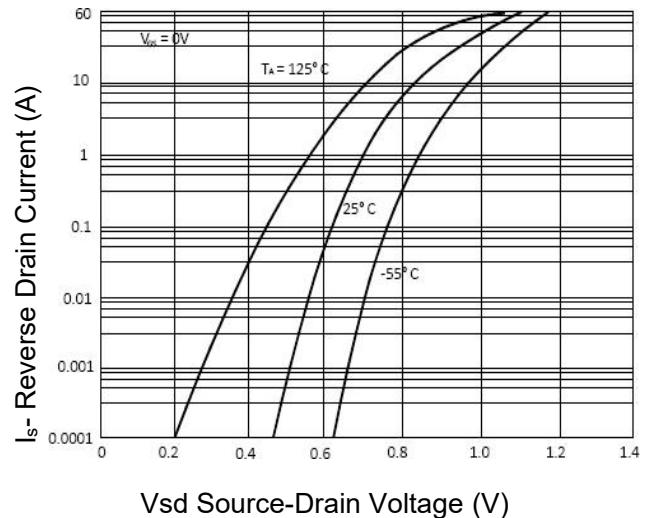


Figure 6 Source- Drain Diode Forward

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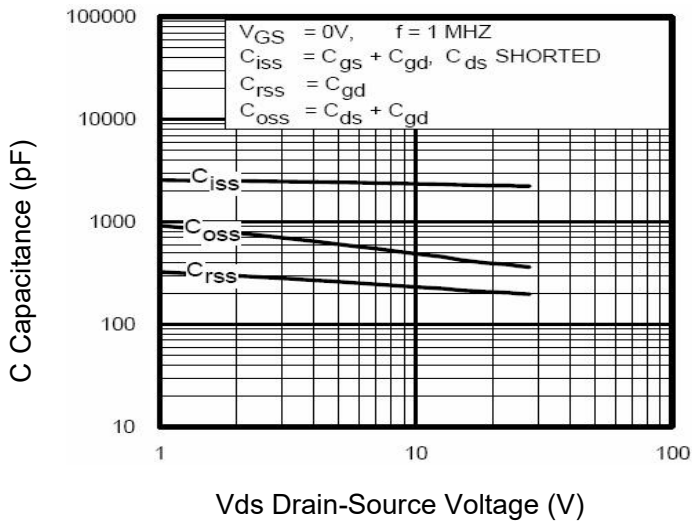


Figure 7 Capacitance vs Vds

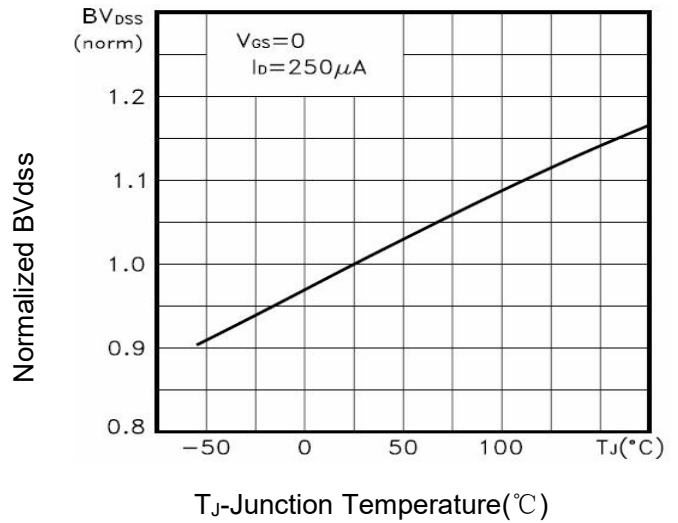


Figure 9 BV_{DSS} vs Junction Temperature

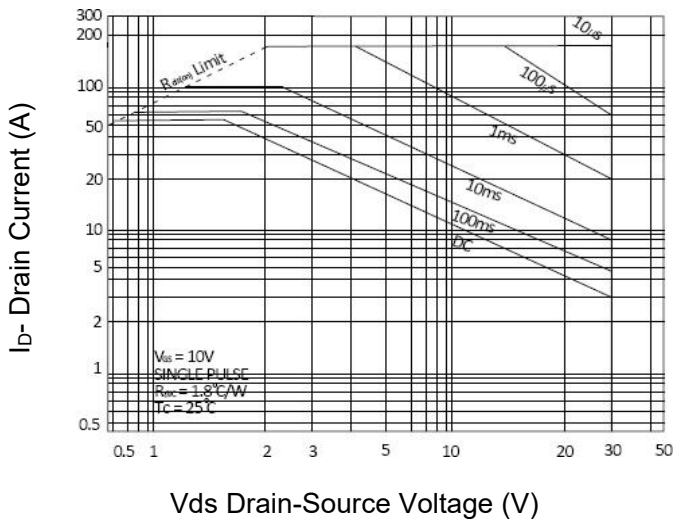


Figure 8 Safe Operation Area

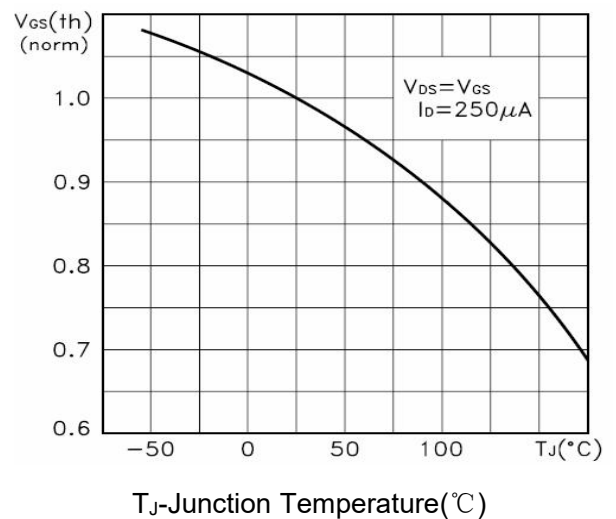


Figure 10 $V_{GS(th)}$ vs Junction Temperature

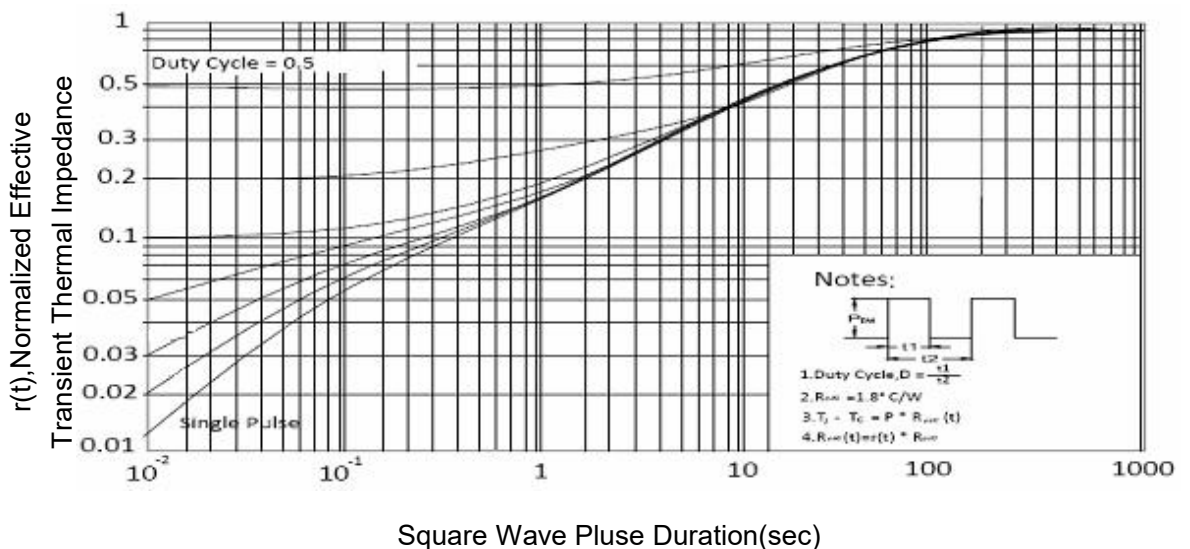
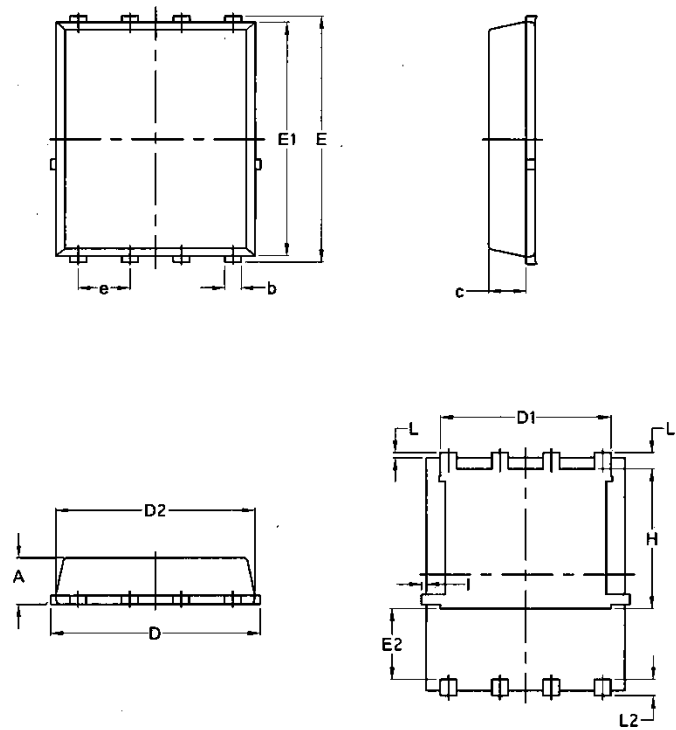


Figure 11 Normalized Maximum Transient Thermal Impedance

Package Mechanical Data:DFN5x6-8L



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

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